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Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.025				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.029				
I _D (A)	40				
Configuration	Single				



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualified
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



COMPLIANT HALOGEN

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD40N10-25-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V_{DS}	100	V		
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current	T _C = 25 °C ^a	1	40			
	T _C = 125 °C	- I _D	26			
Continuous Source Current (Diode Conduct	I _S	40	Α			
Pulsed Drain Current ^b		I _{DM}		160		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	40			
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	80	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	Ъ	136	14/		
	T _C = 125 °C	P_{D}	45	W		
Operating Junction and Storage Temperatu	re Range	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient F	PCB Mount ^c	R_{thJA}	50	°C/W		
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					ı	l .	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		-	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 40 A	-	0.019	0.025	Ω
Dunin Course On Chata Basistanas		V _{GS} = 10 V	I _D = 40 A, T _J = 125 °C	-	-	0.050	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.063	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.021	0.029	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 40 A		-	73	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2703	3380	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	312	390	
Reverse Transfer Capacitance	C _{rss}			-	127	160	
Total Gate Charge ^c	Qg			-	46	70	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 40 \text{ A}$	-	8.2	=-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	13	=-	
Gate Resistance	R _g		f = 1 MHz		2	3.1	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	11	17	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 1.25 Ω $I_D \cong$ 40 A, V_{GEN} = 10 V, R_g = 1 Ω		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41	
Fall Time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Char	acteristics ^b	•					
Pulsed Current ^a	I _{SM}			-	-	160	Α
		I _F = 40 A, V _{GS} = 0 V					V

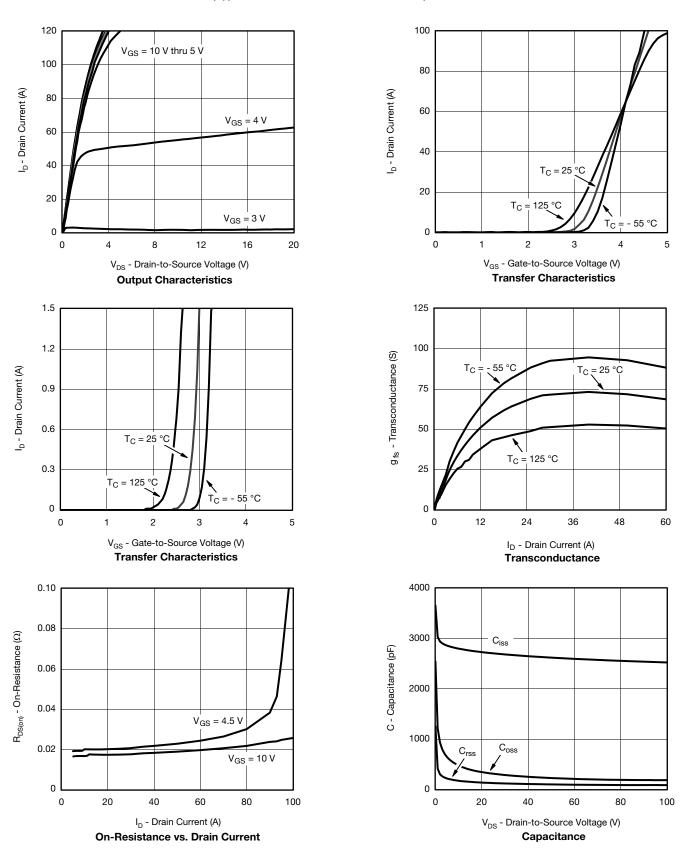
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



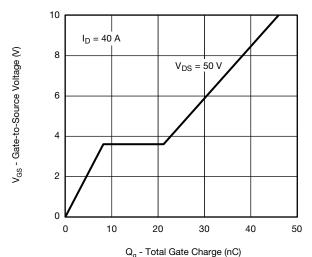
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



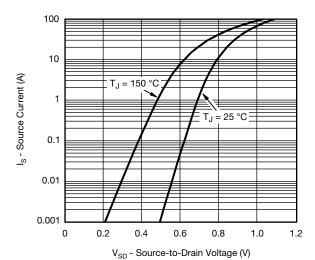
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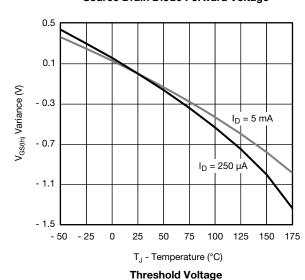
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

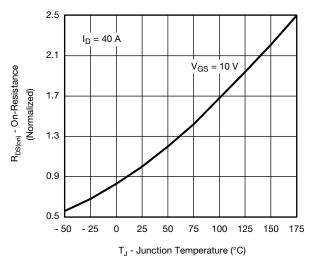




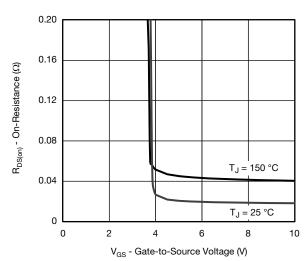


Source Drain Diode Forward Voltage

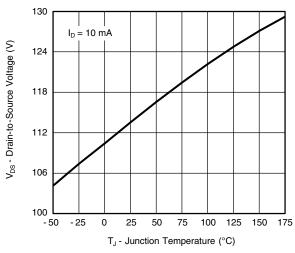




On-Resistance vs. Junction Temperature



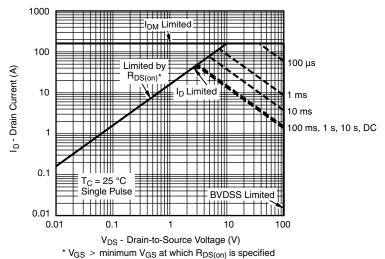
On-Resistance vs. Gate-to-Source Voltage



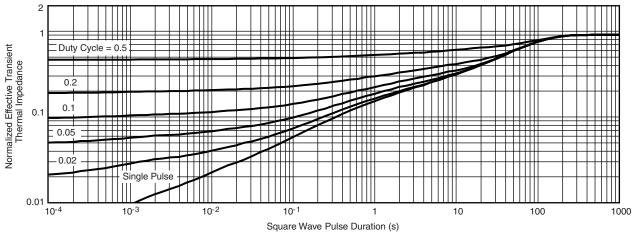
Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

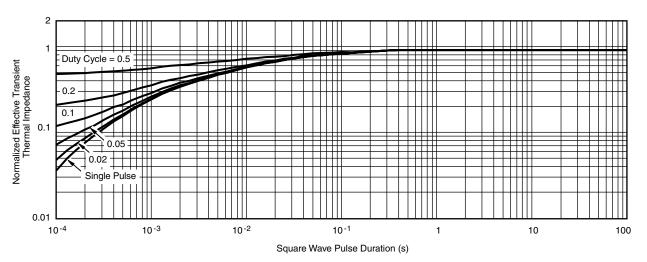


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



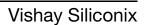
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

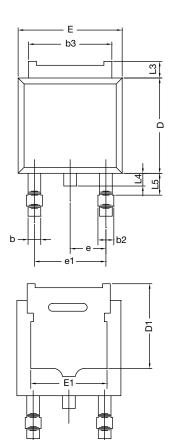
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

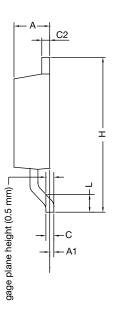
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg269064.





TO-252AA Case Outline



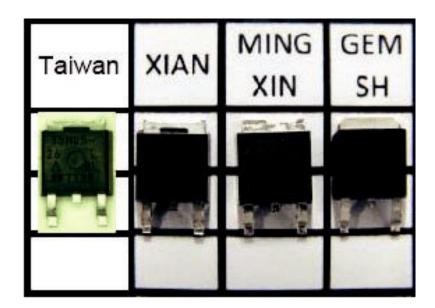


	MILLIN	METERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	4.10	-	0.161	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090	BSC		
e1	4.56	BSC	0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.01	1.52	0.040	0.060		
ECN: T13-0359-Rev. O, 03-Jun-13						

DWG: 5347

Notes

- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13 Document Number: 71197



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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